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(54) **PHOTODIODE STRUCTURE**

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(57) **ABSTRACT**

A photodiode structure is provided, which includes a first electrode, a semiconductor structure, a first anti-reflective layer, a second anti-reflective layer, a second electrode, and a blocking structure. The semiconductor structure is located on the first electrode. The first anti-reflective layer is located on the semiconductor structure layer. The second anti-reflective layer is located on the first anti-reflective layer. The second electrode is located on the second anti-reflective layer and penetrates the first anti-reflective layer and the second anti-reflective layer to electrically connect the semiconductor structure. The blocking structure is arranged between the first anti-reflective layer and the second electrode to prevent the first anti-reflective layer from directly contacting the second electrode.

